PATENT
81788.0020

AFTER FINAL RESPONSE UNDER 37 C.F.R. §1.116
EXPEDITED PROCEDURE

#15/ Amdt'd
R. Tyson
1/23/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Shota Kitamura, et al.

Serial No: 09/392,865

Filed: September 9, 1999

For: NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE AND ITS MANUFACTURING METHOD

Art Unit: 2811

Examiner: T. Tran

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: BOX AF, Assistant Commissioner for Patents, Washington D.C. 20231, on

January 5, 2001
Date of Deposit

William H. Wright
Name

1/5/01
Date

Signature

AMENDMENT AND RESPONSE

UNDER 37 C.F.R. §1.116

BOX AF
Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

This is in response to the final Office Action dated July 5, 2000, which was paper #12 of the present application. Please amend the present application as follows:

IN THE CLAIMS:

Subt D2

Please amend claim 17 as follows:

17. (Amended) The nonvolatile semiconductor memory device according to claim 16, [wherein] further comprising:

[memory regions extending in one direction and] element separating regions extending [in said] along one direction [are alternately formed;], wherein

[in each of said memory regions,] groups of said memory transistors are arranged [in] along said one direction and adjacent said element separating regions;

in each of said element separating regions, an element separating insulating film is formed on said substrate[, and extends] extending in said one direction;

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